

**AMENDMENTS TO THE SPECIFICATION**

Please replace the abstract with the following:

A semiconductor device includes ~~grooves~~ gaps formed in a semiconductor substrate to provide an inner portion movable in x and y directions. Drive electrodes vibrate the inner portion in the x direction, and detection electrodes detect movement in the y direction generated when an angular velocity is applied thereto. Monitor electrodes generate monitor signals for monitoring movement of the inner portion in the x direction. Shield wires are provided between the drive and detection electrodes and the monitor electrodes to suppress capacitive coupling. Dummy electrodes adjacent to the output electrodes and capacitively coupled to the drive electrodes generate a dummy signal. Dummy signal wires are respectively connected to the dummy electrodes and to the circuit substrate. The dummy signal includes an induced component of a periodical signal and is supplied to the circuit substrate to cancel another induced component of the periodical signal in the drive and monitor signals.

**AMENDMENTS TO THE SPECIFICATION**

Please amend the substitute specification submitted on May 20, 2004, as follows:

Please replace the paragraph on page 8, lines 8-12, with the following:

In Fig. 4, the proto-type of semiconductor device is formed with an SOI (silicon on insulator) substrate in which first and second silicon substrates are adhered with adhesive to each other through an oxide film by providing ~~grooves~~ gaps, pads, and wires through well-known semiconductor processes.

Please replace the paragraph on page 8, lines 17-19, with the following:

The second silicon substrate 12 is processed to have ~~grooves~~ gaps therein by micro-machining process or the like to provide following parts:

Please replace the paragraph on page 8, lines 20-23, with the following:

A movable portion 30 is formed to have a substantially rectangular plate shape above the opening 14 by forming ~~grooves~~ gaps surrounding it except elastically connecting portions, i.e., driving beams 33 and detection beams 34. That is, the movable portion 30 is formed inside the frame 20.

Please replace the paragraph from page 11, line 17, through page 12, line 2, with the following:

The semiconductor device shown in Fig. 1 has substantially the same structure as one shown in Fig. 4. That is, the first substrate 11 is supported by the circuit substrate K1. The first substrate 11 has the opening 14. The second substrate 12 and the electrodes are supported by the

first substrate 11 through the oxide film 13. The movable portion is supported above the opening 14 by the drive beams 33. Forming ~~grooves~~ gaps in the second substrate 12 with electrical insulation provides the drive electrodes 40, the detection electrodes, the monitor electrodes 60, the driving beams 33, the detection beams 34, and movable space around the movable portion 30.

Please replace the paragraph on page 17, lines 11-16, with the following:

To reduce this effect, dummy electrodes 80 are formed on the oxide film 13 at the edge of the opening 14 near the detection electrodes 50 and the monitor electrodes 60 by providing ~~grooves~~ gaps around them. The dummy electrodes 80 also have pads 81 formed with aluminum which are electrically connected to the circuit substrate K1 with wires 82.